## Mask Layouts

Single Layer Mask<br>( single field centered within the plate)



## Mask Layouts

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\begin{aligned}
& \text { Single Layer Mask } \\
& \text { ( single field centered within the plate) } \\
& \text { Mask Placement and Polarity }
\end{aligned}
$$



Exposure Field (red circle) $D=100 \mathrm{~mm}$

Large Square (blue box), max die size ( $74 \times 74$ ) mm2


This part of your mask will not be properly exposed

The blue box in the middle is the largest single square size (die size $\sim(14.8 \times 14.8) \mathrm{mm} 2$ that you can shoot on the wafer. This is because the "spot" size on the wafer is 20 mm , mask scale is 5 x ( 100 mm ). Anything outside the red circle is not going to be exposed properly. There will be some bleed through but the features will be under expose.

Mask plate (5x5)" ~ (127x127)mm2

## Quarter with BL orientation writing the program TESTQ

## Die Layout on Quarter



- AUTOSTEP200: LOG IN [10,1]
- CHUCK:142 (for $1 / 4$ of 2" pieces or smaller substrates then 2" )
- Diameter $=55 \mathrm{~mm}$ ( if $\mathbf{1 / 4}$ of $\mathbf{2}$ inch)
- Cell size (die size):
$X=7.5750 \mathrm{~mm}, Y=8.0000 \mathrm{~mm}$
- Gap between die=0.5mm
- $\quad$ Step size (step from die to die):
$X=8.0750 \mathrm{~mm}, \mathrm{Y}=8.5000 \mathrm{~mm}$
- Distance from DIE center to the lower left corner:
$\mathrm{X} / 2=3.7875 \mathrm{~mm}$
$\mathrm{Y} / 2=4.0000 \mathrm{~mm}$
- Adding 1 mm from the corner in $X$, and $Y$ direction bring coordinates for $\mathrm{x}, \mathrm{y}$ :
$X=3.7875+1.0=4.7875 \mathrm{~mm}$
$Y=4.0000+1.0=5.0000 \mathrm{~mm}$
- This is the pass shift for BL orientation:

PASS SHIFT: $x=+4.7875, y=-5.0000$

First layer (Layer\#1 or your first lithography) Running the job: EX TESTQ, pass: 1
BL: Left objective (R3, C1), Right objective (R3, C3),
Press "A" on the key board, the stage moves, and left objective should be positioned above R3C1
Find the lower left corner of your substrate Press "D"(to switch movement from die to die) Aligning takes time (align well along $x$ - axis, and $y$-axis)! The left objective should be positioned above R3C1 prior exposing
Key offset is : $x=0, y=0$; PASS SHIFT: $x=+4.7875, y=-5.0000$


## How



If 0.5 mm is added along the edges ( $x, y$ ). In my calculation I added 1 mm along the edges!

## How to align

- Find the proper chuck, load the sample on the chuck, use screws to help in positioning the sample always at the same place (turn ON the vacuum)
- Load chuck on the stage (turn ON the vacuum)
- Press "A" on the keyboard to move the stage, so LEFT objective is above die R3C1
- Find the BL corner
- Press button " D " on the key board, and press on arrow $\rightarrow$ to step from die to die. Be careful, step as many times as the number of dies you have in that direction ( if you have 3 columns, you can step 3 X ). Be slow and meticulous. Stay on the sample.
- If you step out of sample you might receive the message " Q" for quit. Press "red" button inside of the chamber and start all over with the aligning
- Once aligning is complete (always use right window on monitor for aligning), go back to die R3C1, so LEFT objective is above die R3C1, press expose
- Watch the numbers on voltmeter (column height). This should be in range of -10 V to 10 V . Ideal focus would be around $0 V$.


## Quarter with BR orientation writing the program TESTQ

## Quarter Orientation B

For Active/Passive, layer will be centered in mask plate. This puts the wafer corner at 4.2875 mm Right and 4.5 mm down from the mask origin (with reference to Die 3)


- AUTOSTEP200: LOG IN [10,1]
- CHUCK:142 (for $1 / 4$ of 2" pieces) or smaller then 2")
- Diameter= $\mathbf{5 5 m m}$ ( if $\mathbf{1 / 4}$ of $\mathbf{2}$ inch)
- Cell size (die size):
$X=7.5750 \mathrm{~mm}, Y=8.0000 \mathrm{~mm}$
- Gap between die $=0.5 \mathrm{~mm}$
- $\quad$ Step size ( step from die to die):
$X=8.0750 \mathrm{~mm}, Y=8.5000 \mathrm{~mm}$
- Distance from DIE center to the lower left corner:
$X / 2=3.7875 \mathrm{~mm}$
$\mathrm{Y} / 2=4.0000 \mathrm{~mm}$
- Adding 1 mm from the corner in $X$, and $Y$ direction bring coordinates for $\mathrm{x}, \mathrm{y}$ :
$X=3.7875+1.0=4.7875 \mathrm{~mm}$
$Y=4.0000+1.0=5.0000 \mathrm{~mm}$
- This is the pass shift for BL orientation:

PASS SHIFT: $x=-4.7875, y=-5.0000$

First layer (Layer\#1 or your first lithography) Running the job: EX TESTQ, pass: 2
BR orientation: L objective (R3,C1), R objective (R3,C3)
Do Not use " $A$ " for this orientation!
Find the lower right corner
Press " $D$ "(to switch movement from die to die)
Aligning takes time (align well along $x$ - axis, and $y$-axis)!
The right objective should be positioned above R3C3 prior exposing Key offset is : $x=0, y=0$; PASS SHIFT: $x=-4.7875, y=-5.0000$


## How to expose first layer (aligning to the LR(lower right)corner of sample))

## Orientation B - BR



If 0.5 mm is added along the edges ( $x, y$ ). In my calculation I added 1 mm along the edges!

## How to align

- Find the proper chuck, load the sample on the chuck, use screws to help in positioning the sample always at the same place (turn ON the vacuum)
- Load chuck on the stage ( turn ON the vacuum)
- Find the BR corner
- Press button " D " on the key board, and press on arrow $\rightarrow$ to step from die to die. Be careful, step as many times as the number of dies you have in that direction. Be slow and meticulous. Stay on the sample.
- If you step out of the sample you might receive the message " Q " and option to quit. Press "red" button inside of the chamber (lower, left side) and you have to start all over with aligning
- Once aligning is complete (always use right window on monitor for aligning), make sure your RIGHT objective is above die R3C3, press expose
- Watch the numbers on voltmeter (column height). This should be in range of -10 V to 10 V . Ideal focus would be around OV .

